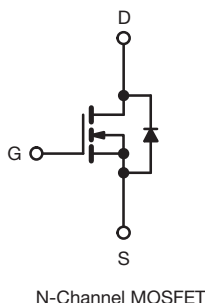


## E Series Power MOSFET with Fast Body Diode and Low Gate Charge

Thin-Lead TO-220 FULLPAK



### FEATURES

- Reduced figure-of-merit (FOM):  $R_{on} \times Q_g$
- Fast body diode MOSFET using E series technology
- Reduced  $t_{rr}$ ,  $Q_{rr}$ , and  $I_{RRM}$
- Increased robustness due to low  $Q_{rr}$
- Low input capacitance ( $C_{iss}$ )
- Reduced switching and conduction losses
- Avalanche energy rated (UIS)
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
Available

### APPLICATIONS

- Telecommunications
  - Server and telecom power supplies
- Computing
  - ATX power supplies
- Industrial
  - Welding
  - Induction heating
  - Battery chargers
  - Uninterruptible power supplies (UPS)
- Renewable energy
  - String PV inverters

### PRODUCT SUMMARY

$V_{DS}$ (V) at $T_J$ max.	650	
$R_{DS(on)}$ typ. ( $\Omega$ ) at 25 °C	$V_{GS} = 10$ V	0.127
$Q_g$ max. (nC)	75	
$Q_{gs}$ (nC)	17	
$Q_{gd}$ (nC)	19	
Configuration	Single	

### ORDERING INFORMATION

Package	Thin-Lead TO-220 FULLPAK
Lead (Pb)-free	SiHA25N60EFL-E3
Lead (Pb)-free and halogen-free	SiHA25N60EFL-GE3

### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	$V_{DS}$	600	V
Gate-source voltage	$V_{GS}$	$\pm 30$	
Continuous drain current ( $T_J = 150$ °C) <sup>e</sup>	$V_{GS}$ at 10 V	$T_C = 25$ °C	A
		$T_C = 100$ °C	
Pulsed drain current <sup>a</sup>	$I_{DM}$	61	
Linear derating factor		2	W/°C
Single pulse avalanche energy <sup>b</sup>	$E_{AS}$	353	mJ
Maximum power dissipation	$P_D$	39	W
Operating junction and storage temperature range	$T_J, T_{stg}$	-55 to +150	°C
Drain-source voltage slope	$dV/dt$	$V_{DS} = 0$ V to 80 % $V_{DS}$	V/ns
Reverse diode $dV/dt$ <sup>d</sup>			
Soldering recommendations (peak temperature) <sup>c</sup>	for 10 s	300	°C
Mounting torque	M3 screw	0.6	Nm


#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature
- $V_{DD} = 140$  V, starting  $T_J = 25$  °C,  $L = 28.2$  mH,  $R_g = 25$   $\Omega$ ,  $I_{AS} = 5$  A
- 1.6 mm from case
- $I_{SD} \leq I_D$ ,  $dI/dt = 100$  A/ $\mu$ s, starting  $T_J = 25$  °C
- Limited by maximum junction

**THERMAL RESISTANCE RATINGS**

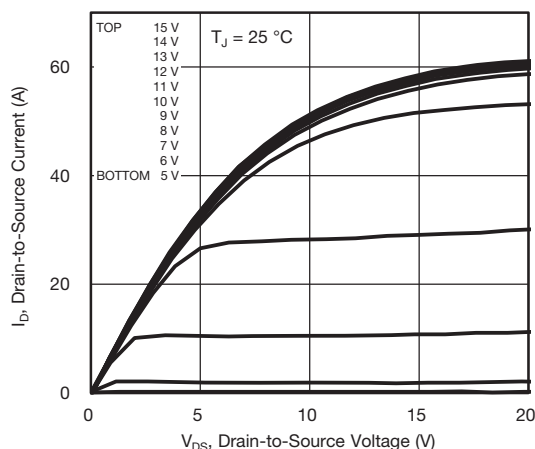
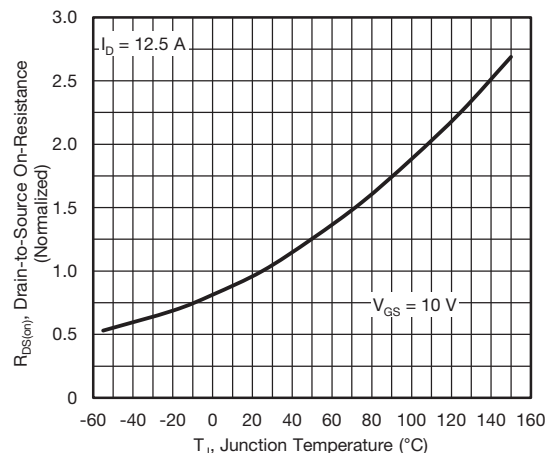
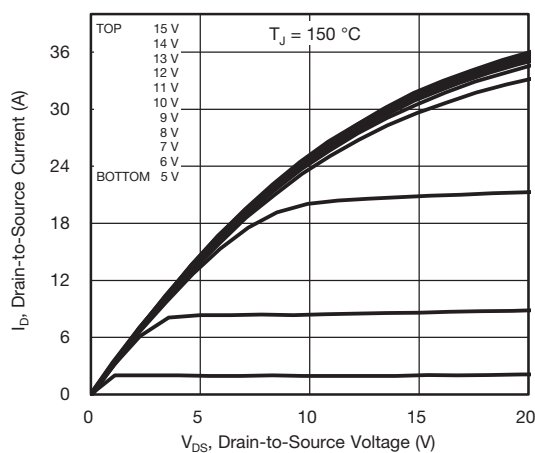
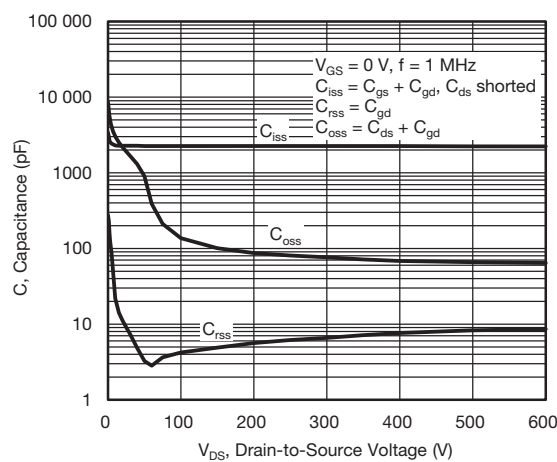
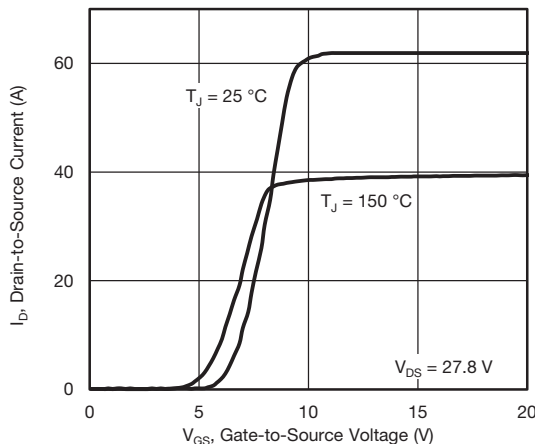
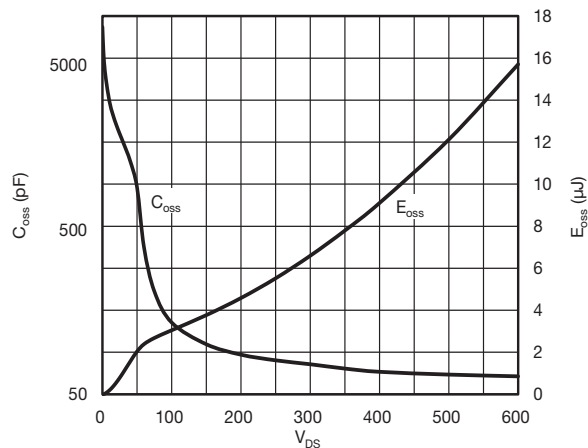
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	$R_{thJA}$	-	65	°C/W
Maximum junction-to-case (drain)	$R_{thJC}$	-	3.2	

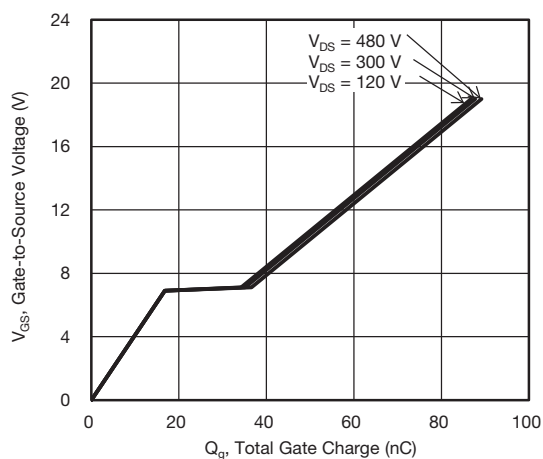
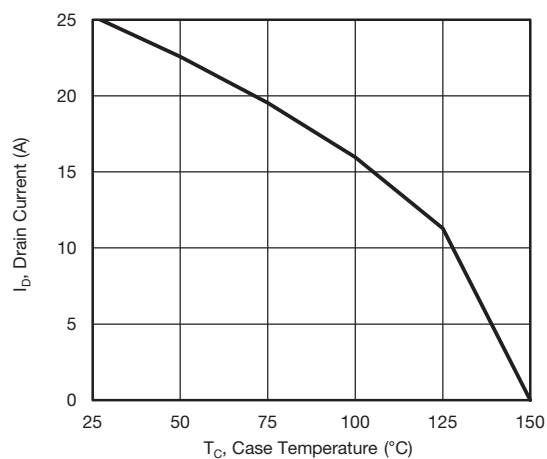
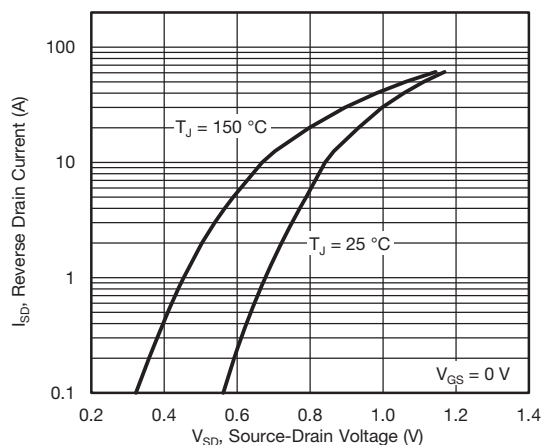
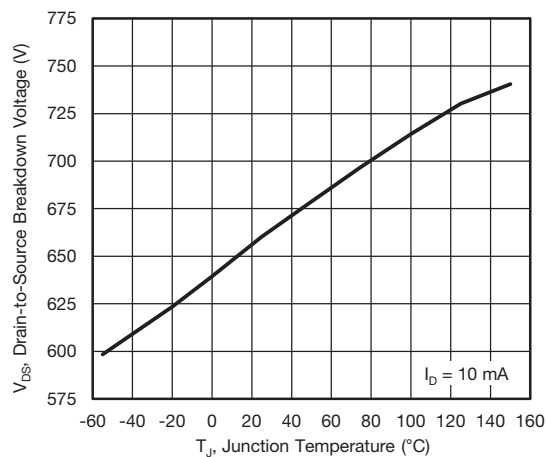
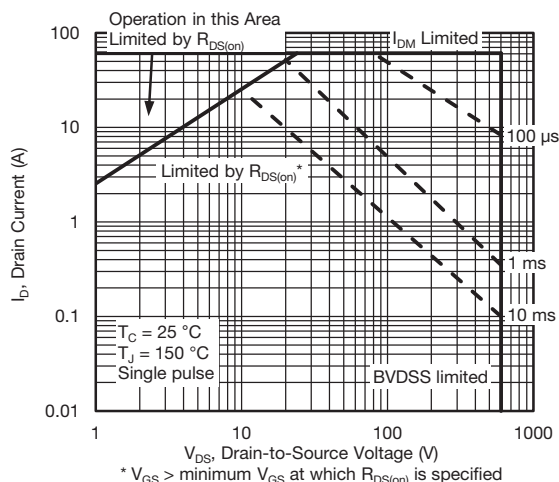
**SPECIFICATIONS** ( $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

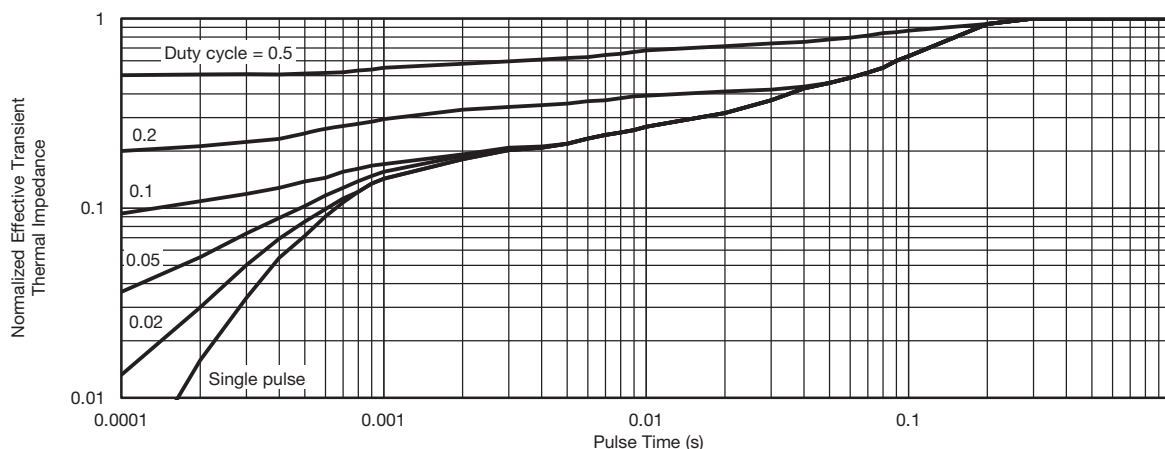
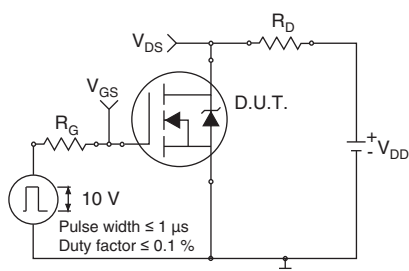
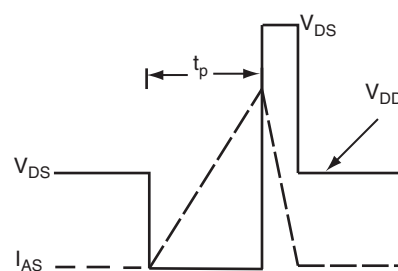
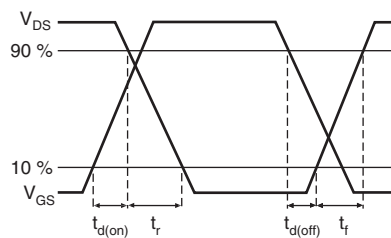
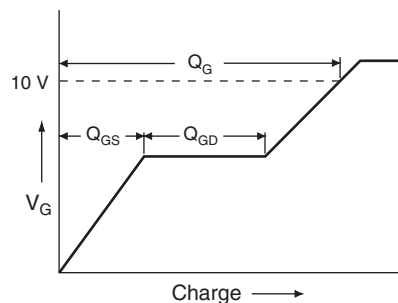
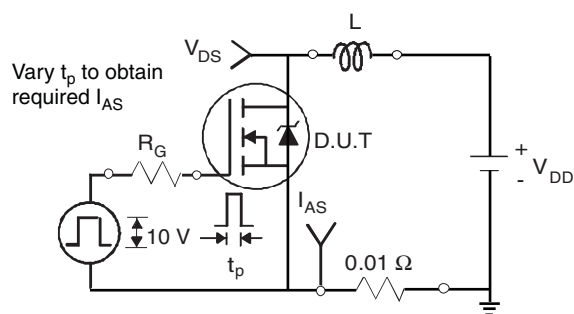
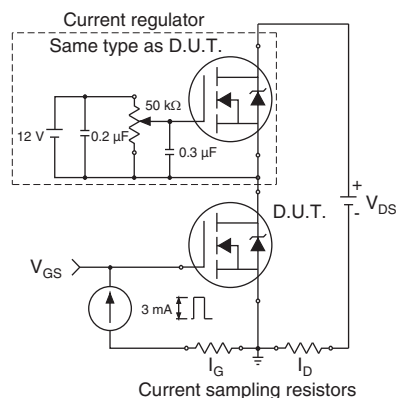
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	$V_{DS}$	$V_{GS} = 0\text{ V}$ , $I_D = 250\text{ }\mu\text{A}$		600	-	-	V
$V_{DS}$ temperature coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$ , $I_D = 10\text{ mA}$		-	0.69	-	V/ $^\circ\text{C}$
Gate-source threshold voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$		3.0	-	5.0	V
Gate-source leakage	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$		-	-	$\pm 100$	nA
		$V_{GS} = \pm 30\text{ V}$		-	-	$\pm 1$	$\mu\text{A}$
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 480\text{ V}$ , $V_{GS} = 0\text{ V}$		-	-	1	$\mu\text{A}$
		$V_{DS} = 480\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 125\text{ }^\circ\text{C}$		-	-	500	
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 12.5\text{ A}$	-	0.127	0.146	$\Omega$
Forward transconductance	$g_{fs}$	$V_{DS} = 30\text{ V}$ , $I_D = 12.5\text{ A}$		-	11.3	-	S
Dynamic							
Input capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}$ , $V_{DS} = 100\text{ V}$ , $f = 1\text{ MHz}$		-	2274	-	pF
Output capacitance	$C_{oss}$			-	137	-	
Reverse transfer capacitance	$C_{rss}$			-	4	-	
Effective output capacitance, energy related <sup>a</sup>	$C_{o(er)}$	$V_{DS} = 0\text{ V to } 480\text{ V}$ , $V_{GS} = 0\text{ V}$		-	79	-	
Effective output capacitance, time related <sup>b</sup>	$C_{o(tr)}$			-	330	-	
Total gate charge	$Q_g$	$V_{GS} = 10\text{ V}$	$I_D = 12.5\text{ A}$ , $V_{DS} = 480\text{ V}$	-	50	75	nC
Gate-source charge	$Q_{gs}$			-	17	-	
Gate-drain charge	$Q_{gd}$			-	19	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 480\text{ V}$ , $I_D = 12.5\text{ A}$ , $R_g = 9.1\text{ }\Omega$ , $V_{GS} = 10\text{ V}$		-	25	50	ns
Rise time	$t_r$			-	39	68	
Turn-off delay time	$t_{d(off)}$			-	47	94	
Fall time	$t_f$			-	21	42	
Gate input resistance	$R_g$	$f = 1\text{ MHz}$ , open drain		0.4	0.7	1.4	$\Omega$
Drain-Source Body Diode Characteristics							
Continuous source-drain diode current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	25	A
Pulsed diode forward current	$I_{SM}$			-	-	61	
Diode forward voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}$ , $I_S = 12.5\text{ A}$ , $V_{GS} = 0\text{ V}$		-	0.9	1.2	V
Reverse recovery time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}$ , $I_F = I_S = 12.5\text{ A}$ , $dI/dt = 100\text{ A}/\mu\text{s}$ , $V_R = 25\text{ V}$		-	138	276	ns
Reverse recovery charge	$Q_{rr}$			-	0.8	1.6	$\mu\text{C}$
Reverse recovery current	$I_{RRM}$			-	11	-	A

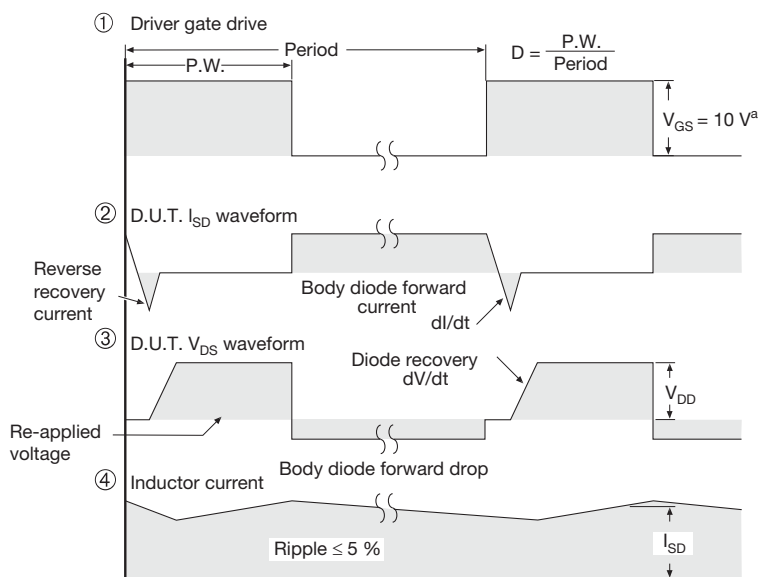
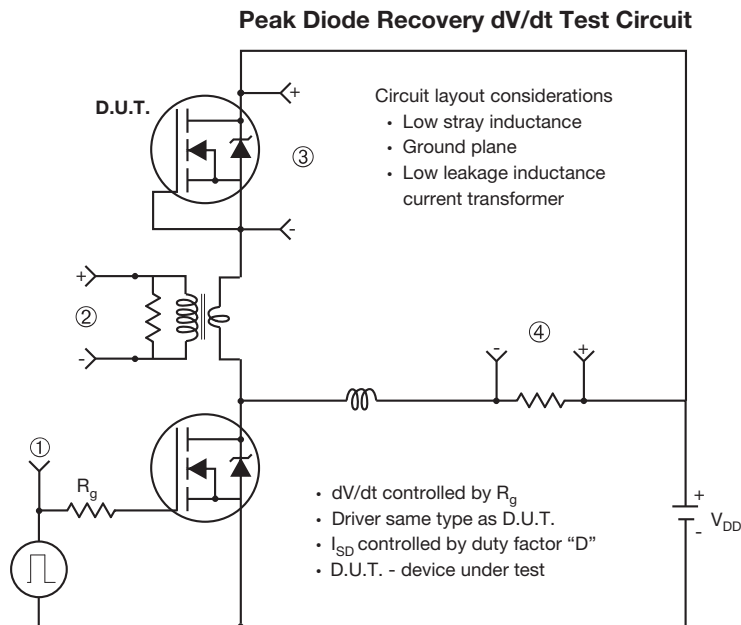
**Notes**

- a.  $C_{oss(er)}$  is a fixed capacitance that gives the same energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$   
b.  $C_{oss(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Fig. 1 - Typical Output Characteristics**

**Fig. 4 - Normalized On-Resistance vs. Temperature**

**Fig. 2 - Typical Output Characteristics**

**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**

**Fig. 3 - Typical Transfer Characteristics**

**Fig. 6 -  $C_{OSS}$  and  $E_{OSS}$  vs.  $V_{DS}$**


**Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage**

**Fig. 10 - Maximum Drain Current vs. Case Temperature**

**Fig. 8 - Typical Source-Drain Diode Forward Voltage**

**Fig. 11 - Typical Drain-to-Source Voltage vs. Temperature**

**Fig. 9 - Maximum Safe Operating Area**


**Fig. 12 - Normalized Thermal Transient Impedance, Junction-to-Case**

**Fig. 13 - Switching Time Test Circuit**

**Fig. 16 - Unclamped Inductive Waveforms**

**Fig. 14 - Switching Time Waveforms**

**Fig. 17 - Basic Gate Charge Waveform**

**Fig. 15 - Unclamped Inductive Test Circuit**

**Fig. 18 - Gate Charge Test Circuit**


**Note**

a.  $V_{GS} = 5\text{ V}$  for logic level devices

**Fig. 19 - For N-Channel**

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